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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	Unassigned
		Filing Date	June 23, 2004
		First Named Inventor	ANDO et al.
		Art Unit	Unassigned 1733
		Examiner Name	Unassigned Hitisheva
Sheet	1	of	1
		Attorney Docket Number 92372	

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.*	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Paragraphs or References Figures Appear	T#
		Country Code-Number-Kind Code-(if known)				
F.H.	JP 07201874		08/04/1995	NEC Corp.		Abstract
F.H.	EP 0 889 510		01/07/1999	Adachi et al.		Yes
F.H.	JP 09194294		07/29/1997	Sumitomo Sitix Corp.		Abstract
SH.	EP 1 035 235		09/13/2000	Tamatsuka et al.		Yes

OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.*	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
F.H.		Adachi, et al.; "Reduction of Grown-In Defects by High Temperature Annealing," <i>Journal of The Electrochemical Society</i> , Vol. 147 (1), pp. 350-353, 2000.	
F.H.		Umeno et al.; "Dependence of Grown-In Defect Behavior on Oxygen Concentration in Czochralski Silicon Crystals," <i>Jpn. J. Appl. Phys.</i> , Vol. 38, Pt. 1, No. 10, pp. 5725-5730, 1999.	
F.H.		Wijaranakula et al.; "Effect of high-temperature annealing on the dissolution of the D-defects in n-type Czochralski silicon," <i>Appl. Phys. Lett.</i> , Vol. 64 (8), pp. 1030-1032, 21 February 1994.	

Examiner Signature	D. Miller	Date Considered	8/2/2096
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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